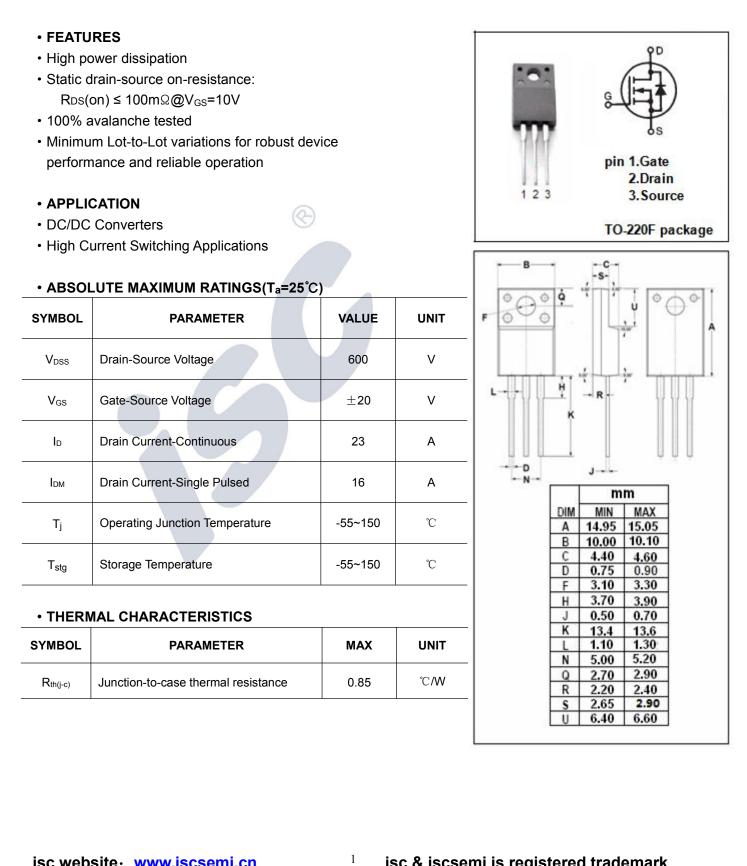


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXKC23N60C5





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IXKC23N60C5

ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25\,^\circ\!\!\!\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID = 250 μ A	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID = 100 μ A	2.5		3.5	V
$R_{\text{DS(on)}}$	Drain-Source On-Resistance	V _{GS} =10V; I _D = 18A			100	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V			2	- μ Α
		V _{DS} = V _{DSS} ; V _{GS} = 0V;TJ= 125℃		50		
V_{SD}	Diode forward voltage	I _F = 16A; V _{GS} = 0V			1.2	V

NOTICE:

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